

Chemical Vapor Deposition

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Solid–Vapor Reaction Growth of Transition-Metal Dichalcogenide Monolayers

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Abstract: Two-dimensional (2D) layered semiconducting transition-metal dichalcogenides (TMDCs) are promising candidates for next-generation ultrathin, flexible, and transparent electronics. Chemical vapor deposition (CVD) is a promising method for their controllable, scalable synthesis but the growth mechanism is poorly understood. Herein, we present systematic studies to understand the CVD growth mechanism of monolayer MoSe₂, showing reaction pathways for growth from solid and vapor precursors. Examination of metastable nanoparticles deposited on the substrate during growth shows intermediate growth stages and conversion of non-stoichiometric nanoparticles into stoichiometric 2D MoSe₂ monolayers. The growth steps involve the evaporation and reduction of MoO₃ solid precursors to sub-oxides and stepwise reactions with Se vapor to finally form MoSe₂. The experimental results and proposed model were corroborated by *ab initio* Car–Parrinello molecular dynamics studies.

The rise of layered two-dimensional (2D) materials has initiated a new era in materials innovation.^[1] Semiconducting transition-metal dichalcogenides (TMDCs) have emerged as promising candidates for next-generation ultrathin, flexible, and transparent electronics.^[1g–k,2] Recent progress in chemical vapor deposition (CVD) has shown that high-quality single crystals and wafer-scale continuous films of controlled thick-

ness can be obtained, driving the development of TMDCs for these applications.^[1j,2d,e,3] Whereas some aspects (e.g., crystal and film size, defects, number of layers) can be controlled,^[2d,3a] the development of CVD methods for the synthesis of TMDCs has reached a bottleneck, and further progress is unlikely if the growth mechanism is not fully understood.

Diverse growth methods and mechanisms have been described for various nanomaterials, including vapor–liquid–solid (VLS) processes for nanowire synthesis^[4] and vapor-phase reactions for TMDC nanoparticles.^[5] The CVD method is one of the most promising techniques for synthesizing large-scale 2D materials,^[1d,e,2d,3a,6] exceeding the size limitations of other methods, such as mechanical exfoliation^[1a] and the catalyst-free vapor–solid (VS) syntheses (demonstrated for MoS₂, Bi₂Se₃, and Bi₂Te₃).^[7] The CVD growth mechanism of graphene has been investigated in detail, and is known to be substrate-dependent.^[8] On Ni substrates, the growth is generally believed to be the precipitation of dissolved carbon, whereas on Cu substrates, it is a catalytic growth process.^[1d,e] The CVD growth of TMDCs, however, involves multiple reactants and products, and is significantly more complicated than graphene growth. Identification of the byproducts formed during TMDC growth is also challenging because post-growth analysis is often prohibited by the formation of contaminants during the cooling process. Therefore, despite tremendous research efforts to grow various TMDC materials^[1i–k,2d,e] and heterogeneous analogues,^[9] the CVD growth process of TMDCs is currently not well understood.

Herein, we analyzed the CVD growth mechanism of 2D MoSe₂. Samples were quenched halfway through a typical CVD growth process and compared to those that were slowly cooled to completion. The intermediate phases in the quenched samples were then analyzed. Based on the co-existence of MoSe₂, aligned nanoparticles (APs) at the crystalline edges of MoSe₂, and randomly distributed nanoparticles (RPs), as well as evidence of an in-plane “feedstock” and MoSe₂ nucleation from the RPs, we developed a three-step growth model and proposed chemical reactions for each step, which were corroborated by molecular dynamics simulations. The first model of the CVD growth process of TMDCs has thus been developed. Furthermore, the growth of MoSe₂ was shown to be a reversible reaction, where the MoSe₂ edges recede during the slow cooling process.

As shown in Figure 1a, a chip of Si/SiO₂ wafer was placed on top of a crucible preloaded with MoO₃ powder in the center of a tube furnace. Se powder was placed upstream of the wafer, and Ar/H₂ (85/15 %) was used as the carrier gas. The furnace was heated to 750 °C from room temperature at

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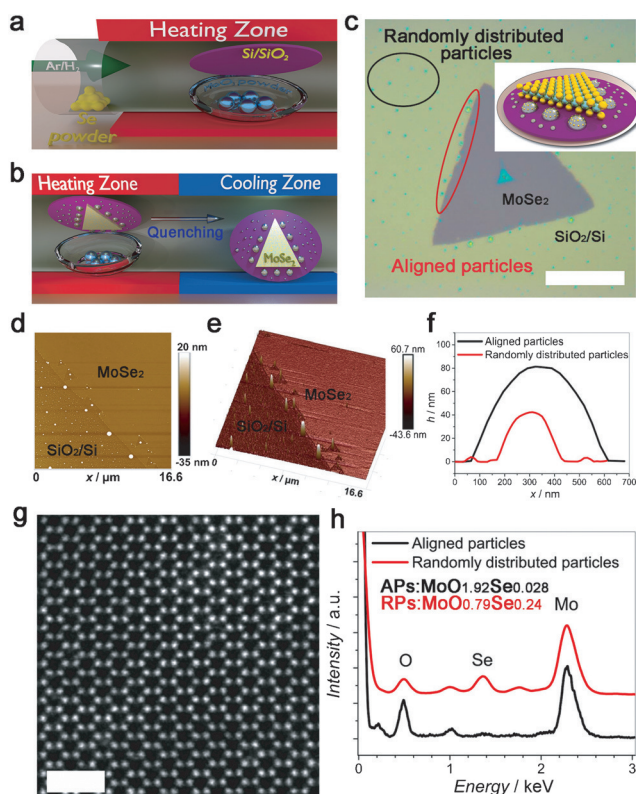


Figure 1. a) The growth process and b) the quenching process. c) Optical image of MoSe₂ grown on a SiO₂/Si substrate together with APs along the edge of MoSe₂ and RPs. Inset: Schematic representation of the quenched substrate. d, e) The AFM topology of the MoSe₂ edge, 2D (d) and 3D (e) views. f) The line profiles of APs near the edge and RPs. The height of the APs was about 80 nm with a diameter of approximately 500 nm. The heights of the RPs are in the range of several nanometers to tenths of nanometers. Overall, the RPs are much smaller than the APs. g) STEM image of monolayer MoSe₂. h) EDX spectra of APs and RPs. The marked peaks of interest for Mo, Se, and O are located at 2.29, 1.37, and 0.51 keV, respectively, with unmarked peaks from the background of Cu (0.99 keV) and Si (1.75 keV). Scale bars: 20 μ m for (c) and 1 nm for (g).

a rate of 50 °C min⁻¹ and then held at 750 °C for the growth of MoSe₂. The quenching procedure was performed by relocating the crucible from the center of the furnace (750 °C) to room temperature (ca. 25 °C) within one second after holding at 750 °C for 10 min (Figure 1b). For comparison, we also performed slow cooling experiments in which a constant cooling rate of 12.5 °C min⁻¹ was applied after heating to 750 °C at the same rate and holding the temperature for 5 to 60 min.

After quenching the growth process at 10 min, three types of components, which were distinctly different in size, composition, and morphology, were found on the substrate. As shown in Figure 1c, triangular-shaped single crystals of MoSe₂ were formed, along with APs at the crystalline edges of MoSe₂ and RPs found elsewhere on the substrate (see the Supporting Information, Figure S1a–f). MoSe₂ gave Raman peaks at 239 cm⁻¹ (A_{1g}) and 285 cm⁻¹ (E'_{2g}; Figure S1g), which is consistent with the A_{1g} and E'_{2g} peaks of single-layer MoSe₂,^[3b,c,10] whereas both the APs and RPs showed no

signature peaks (Figure S1h,i). At the edges of the single crystals, well-ordered lines of APs are present, with a diameter of about 500 nm and a height of approximately 80 nm, as determined by atomic force microscopy (AFM; Figure 1d–f). The RPs, which were randomly dispersed away from the crystalline edges, are much smaller and have a wider size distribution, with diameters ranging from several nanometers to as large as about 200 nm and heights from several nanometers to tens of nanometers (Figure 1c–f; see also Figure S1). High-angle annular dark field (HAADF) scanning transmission electron microscopy (STEM; Figure 1g) confirmed the highly crystalline nature of the MoSe₂ monolayer. High-resolution STEM images of the APs and RPs were unattainable as their size precluded penetration by the electron beam. Instead, selected area electron diffraction (SAED; Figure S2b,g) and energy-dispersive X-ray spectroscopy (EDX; Figure 1h and Figure S2c–e, h–j) analysis were performed to determine the structure and composition of these particles. The EDX results were obtained by accumulating the mapping results of multiple particles as shown in Figure 1h (see also Figure S2). The marked peaks of interest for Mo, Se, and O are located at 2.29, 1.37, and 0.51 keV, respectively, with unmarked peaks from the background of Cu (0.99 keV) and Si (1.75 keV). The atomic ratio of the RPs according to the mapping analysis is MoO_{0.79}Se_{0.24}, with the entire index normalized to the Mo content. The atomic ratio of the APs is MoO_{1.92}Se_{0.028}; the oxygen content is almost two while the Se content is substantially diminished. The SAED patterns indicate that both the APs and RPs are amorphous (Figure S2b,g).

Considering the striking differences in the atomic composition and the distribution of the two types of nanoparticles, we suggest a unique growth mechanism that has never been considered for 2D layered TMDC growth. The growth of graphene and TMDC fullerene-like nanoparticles (with a similar chemical composition but a different morphology to TMDC 2D layers) is generally believed to be a vapor-phase reaction.^[1d,e,5a] However, in this case, the presence of different MoO_xSe_y nanoparticles and their potential for subsequent selenization suggest that the CVD growth of MoSe₂ could be a solid- or liquid-phase reaction where the nanoparticles serve as a reactant. The alignment between the edge of MoSe₂ and the APs suggests that the APs are byproducts of the MoSe₂ growth. The size distribution of the RPs indicates that they are coarsening particles formed by the condensation process during the CVD growth, as shown in Figure 1d–f (see also Figure S1). One argument might be that these two types of nanoparticles are condensed phases that are formed during the fast cooling process. However, if this is true, the two types of nanoparticles should have similar compositions and spatial distributions as the gas-phase environment near the substrate should be uniform. However, the compositions and sizes of APs and nearby RPs are different.

The proposition that the RPs are an intermediate reactant for MoSe₂ growth arose from the observation of multilayered MoSe₂ with the top layer containing a shaped domain looking like the “radioactive warning sign” (Figure 2a). We hypothesized that the three triangular grains seen in this domain are likely to have grown from small adjacent MoSe₂ nuclei with

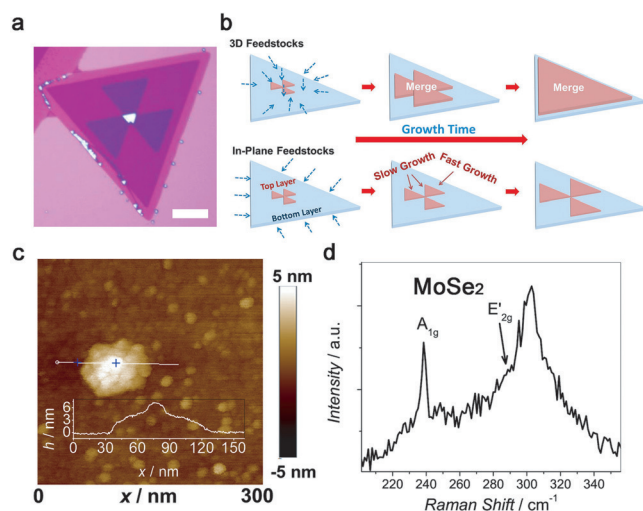


Figure 2. a) Trilayer MoSe₂ with a radiation-signal grain on the top layer. Scale bar: 10 μm. b) The evolution of a small radiation-signal grain on the top of the bottom layer in different feedstock modes. In the 3D feedstock mode, the three grains will grow and merge and eventually become a large triangle. In the in-plane feedstock mode, with at least one of the necessary reactants supplied from within the plane, the differences in diffusion length will cause a faster growth at the edges close to the reactant and slower growth at the inner edges, leading to separate triangles. c) AFM image of an RP after annealing at 700 °C for 10 min with the same H₂/Ar environment, but no Se and MoO₃ sources. The hexagonally shaped nucleus was developed from an RP. Inset: Line profile of the nanoparticle along the white line in (c). d) Raman spectrum of the nucleus showing the representative MoSe₂ signals.

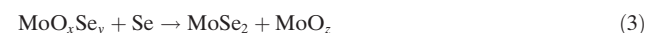
the same crystalline orientation on the top of the bottom layer. If the growth of these nuclei was isotropic, as from a three-dimensional (3D) gas-phase feedstock, they should have quickly merged and formed a single grain (schematically shown in Figure 2b, top) instead of three individual grains. However, as illustrated in Figure 2b (bottom), the observed domain morphology may arise if the domain growth relies on the in-plane (inward) diffusion of the Mo feedstock from the surrounding RPs on the substrate. Such a reactant diffusion process could cause the outer edge of the triangular grain to grow faster than the two inner edges owing to the shorter diffusion distance, and hence, it receives a larger diffusion flux. Collectively, the experimental results presented above reveal that the vapor-phase growth mechanism proposed for both graphene and TMDC nanoparticles is not valid for the growth of layered TMDCs.

Assuming that the RPs are a necessary reaction intermediate, we hypothesized that the RPs form the nuclei of the single crystals during growth. To confirm this hypothesis, a quenched sample was annealed at 700 °C under the same reducing environment (H₂/Ar) for 10 min with no supply of Se or MoO₃. The subsequent AFM image shows the formation of a hexagonal nucleus with a thickness of 6 nm (Figure 2c) that exhibited the characteristic Raman signatures of MoSe₂, A_{1g} at 239 cm⁻¹ and E'_{2g} at 285 cm⁻¹ (observed as a shoulder peak under the background peak of Si at 300 cm⁻¹ in Figure 2d). This result suggests that even in RPs, which are Se-deficient

(the Mo content is more than 4 times greater than that of Se), MoSe₂ nuclei “precipitate” from Mo-rich RPs at high temperature without further supply of Se or Mo. This experiment provides the first direct observation of the formation of MoSe₂ nuclei preceding single-crystal growth.

To further confirm that the RPs are a reactant in MoSe₂ growth, we estimated the total volume of RPs in representative regions of the AFM images based on the height profiles. Simple calculations show that the amount of Mo atoms available in the RPs in these regions is sufficient to form a ten-layer MoSe₂ crystal that covers the entire region. Moreover, the amount of Mo in the RPs was found to be much greater than that in MoSe₂ and APs combined in quenched samples (Figure S3 and S4 and Section S3). This result suggests that the RPs can indeed supply a sufficiently large amount of Mo atoms to facilitate MoSe₂ growth.

Given the central role of the RPs as reaction intermediates in the CVD growth of MoSe₂, we propose the following three-step growth model: I) reduction and evaporation of MoO₃ to a Mo suboxide (MoO_x, 0 < x < 3), II) co-condensation of the Mo suboxide and Se into RPs, III) selenization of the RPs by the vapor-phase Se to form MoSe₂ and APs (Figure 3a). In step I, MoO₃ is reduced by H₂ (15 %)/Ar gas to form MoO_x and H₂O. The value of x (x = 0.79) was determined from the composition of the RPs. This step has been well-established by Feldman et al., and the sublimation temperature of MoO_x (0 < x < 3) can be as low as 650 °C, which is well below the temperature (750 °C) used in our CVD process.^[5c] In step II, reduced MoO_x vapor interacts with the Se vapor phase and condenses on the wafer, forming RPs with the composition MoO_xSe_y (x = 0.79, y = 0.24). It is interesting to note that adding a small amount of Se leads to significant MoO_x condensation. The RPs are composites of reduced MoO_x and Se, not compounds with fixed stoichiometry, which was confirmed by the fact that the composition of the RPs varies from point to point (MoO_xSe_y, 0.22 < x < 1.25, 0.13 < y < 0.5; Figure S2c–e and Table S1). Finally, in step III, the RPs react with vapor-phase Se to form MoSe₂ and expel oxygen into the O-rich APs that decorate the edges of the MoSe₂ crystals. The reactions involved in the three-step model can be written as:



The proposed mechanism was supported by Car–Parriello molecular dynamics (CPMD) simulations.^[11] Our starting structural model is a single-layer MoSe₂ crystal, and single molecular/atomic species (Mo–O and/or Se) were added from a distance of about 5.2 Å away from the Se-terminated zigzag edge step by step (Figure 3b; both front and top views of each step are presented). This distance was determined to be far enough to prevent initial interactions between added species and the MoSe₂ edge but close enough to allow for interactions to occur within the simulation time. The system was allowed to evolve freely in time. As the RPs are a condensed

that Se and a less-reduced MoO_x species from the vapor phase continuously deposit, changing the composition of the APs during the cooling process. This result confirms that Se is too slow to diffuse into the rapidly growing APs during the growth process. Moreover, the change in the composition of the APs during slow cooling suggests the unique advantage of the quenching technique in obtaining in situ information on the growth process.

It is also interesting to note that the reaction to form MoSe_2 is reversible, and a receding of the growth front and nanoparticle regrowth can be observed in the slow-cooled samples after different growth times (Figure 4 and Figure S7).

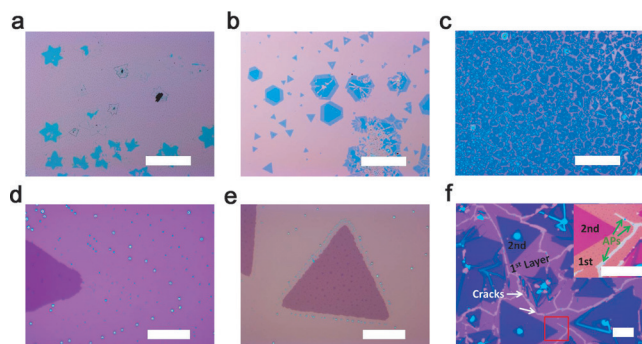


Figure 4. The degradation of MoSe_2 during slow cooling at a cooling rate of $12.5^\circ\text{C min}^{-1}$. Optical images of slowly cooled samples heated to 750°C and held at that temperature for different periods of time: a, d) 5 min, b, e) 10 min, c, f) 60 min. Scale bars: $400\ \mu\text{m}$ in (a)–(c) and $20\ \mu\text{m}$ in (d)–(f) and the inset.

We have demonstrated that the APs will decorate the growth front after quenching (the distance between the APs and the front ranges from 0 to about $200\ \text{nm}$) and can be used as markers for the original location of the MoSe_2 single-crystal edges. In sharp contrast, larger gaps of about $30\ \mu\text{m}$ after 5 min growth and approximately $1\text{--}2\ \mu\text{m}$ after 10 min growth were observed for slowly cooled samples (Figure 4a and d, b and e). We surmise that the observed variation in gap width is correlated with the quality of the MoSe_2 crystals; MoSe_2 grown for a shorter period of time (e.g., the 5 min sample) tends to be more defective, and the edge is thus “etched” away at a higher rate during slow cooling than those grown for a longer time. This hypothesis was confirmed by a third sample with an extremely long growth time (60 min) in which the MoSe_2 displayed no signs of degradation (Figure 4c and f). Here, the APs are sandwiched in the gaps between nearby crystals.

Finally, it is important to note that these nanoparticles (both APs and RPs) have also been observed in the CVD growth of other TMDC materials (such as MoS_2 and WSe_2 ; Figure S8), highlighting the active role of the nanoparticles in the growth process as well as in understanding the growth mechanism. Therefore, we believe that this growth model and method could provide general insight into the CVD growth of all TMDCs.

In conclusion, we have presented the first comprehensive analysis of the CVD growth mechanism of atomic-layered TMDCs. Unlike the generally accepted vapor-phase reaction

mechanisms for graphene and TMDC nanoparticles, this mechanism demonstrates the important role of a metastable nanoparticle reaction intermediate ($\text{MoO}_{0.79}\text{Se}_{0.24}$), which serves as both the direct source of Mo and the nucleation site for the formation of layered MoSe_2 . Quenching and long-time growth experiments also highlight strategies to obtain high-quality TMDCs, and suggest the reversibility and in-plane nature of the growth process. With similar phenomena observed for other layered TMDCs, we believe that this investigation will lead to further progress in improving the crystalline quality and large-area growth of these exciting 2D materials.

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